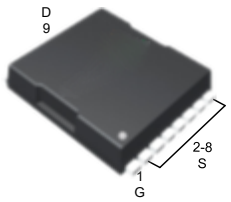
Features

- 60V/260A,
  $R_{DS(ON)}$= 2mΩ(typ.) @ V_{GS}= 10V
- 100% UIS+Rg Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

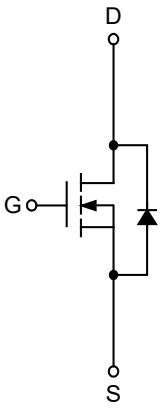
Pin Description



TOLL

Applications

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching



N-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		±25	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	
I_S	Diode Continuous Forward Current	T_C=25°C	260	A
I_D	Continuous Drain Current	T_C=25°C	260	
	Continuous Drain Current	T_C=100°C	195	
I_{DM}	Pulsed Drain Current	T_C=25°C	780	
P_D	Maximum Power Dissipation	T_C=25°C	312	W
		T_C=100°C	125	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	0.4	°C/W
$R_{\theta JA}$ *	Thermal Resistance-Junction to Ambient	Steady State	50	°C/W
I_{AS} c	Avalanche Current, Single pulse	L=0.5mH	65	A
E_{AS} c	Avalanche Energy, Single pulse	L=0.5mH	1056	mJ

Note *: Surface Mounted on 1in^2 pad area.
Note a: Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 120A.
Note b: Pulse width limited by max. junction temperature.
Note c: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_j=25°C).

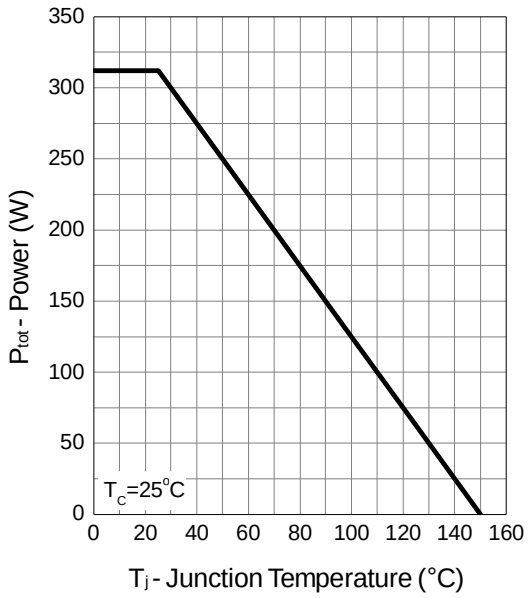
Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=48V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	2	3	4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±25V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=40A	-	2	2.4	mΩ
Diode Characteristics						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=20A, V_{GS}=0V	-	0.8	1.3	V
t_{rr}	Reverse Recovery Time	I_{DS}=40A, dI_{SD}/dt=100A/μs	-	65	-	ns
Q_{rr}	Reverse Recovery Charge		-	117	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	1	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=30V, Frequency=1.0MHz	-	9000	11700	pF
C_{oss}	Output Capacitance		-	1525	-	
C_{rss}	Reverse Transfer Capacitance		-	710	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=30V, R_L=30Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	40	72	ns
T_r	Turn-on Rise Time		-	20	36	
$t_{d(OFF)}$	Turn-off Delay Time		-	102	184	
T_f	Turn-off Fall Time		-	82	148	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=30V, V_{GS}=10V, I_{DS}=40A	-	172	240	nC
Q_{gs}	Gate-Source Charge		-	40	-	
Q_{gd}	Gate-Drain Charge		-	55	-	

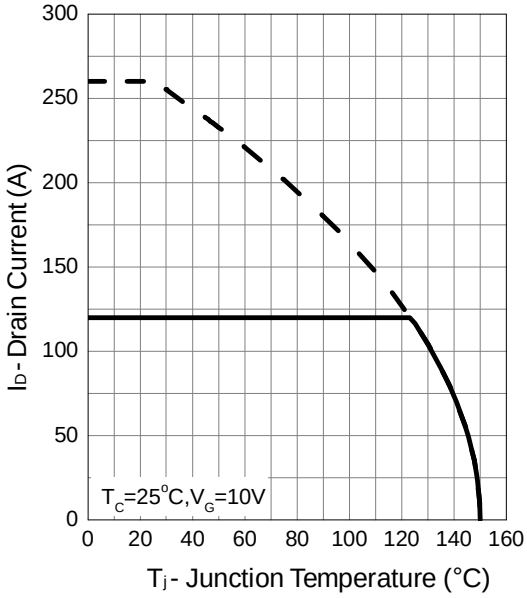
Note d: Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e: Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

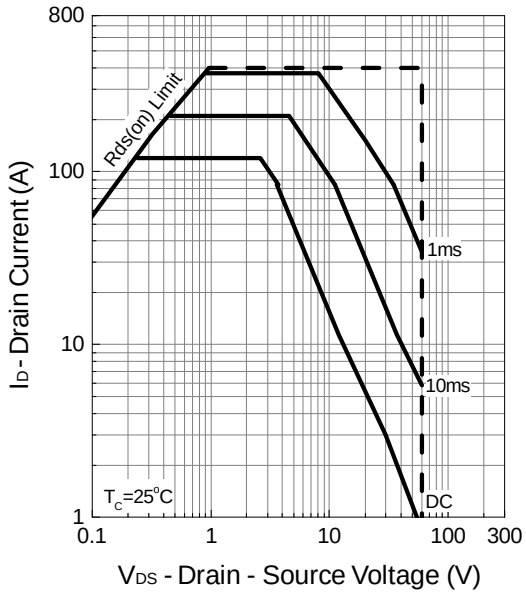
Power Dissipation



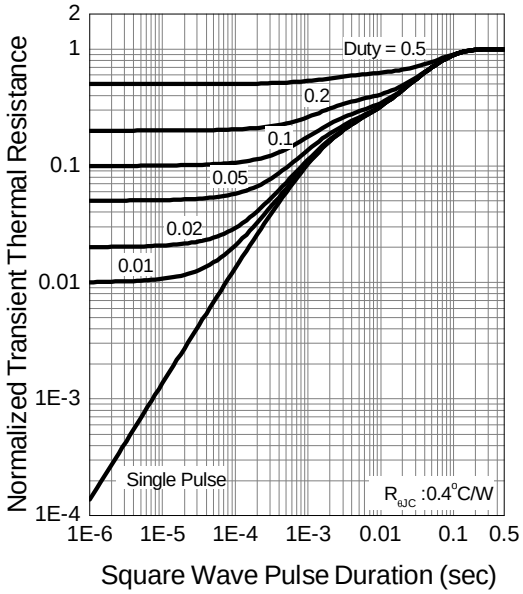
Drain Current



Safe Operation Area

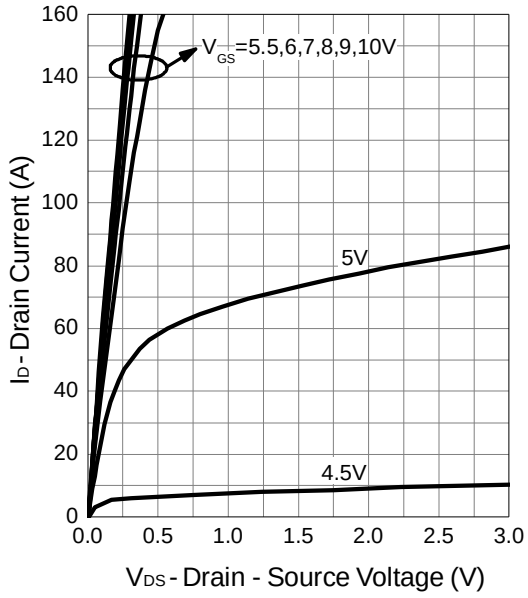


Thermal Transient Impedance

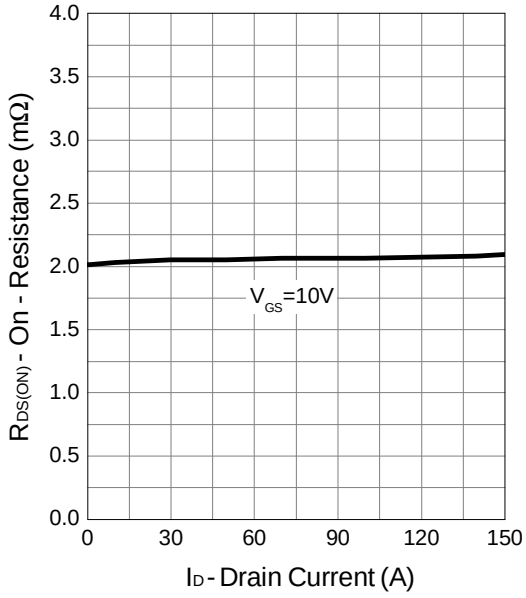


Typical Operating Characteristics (Cont.)

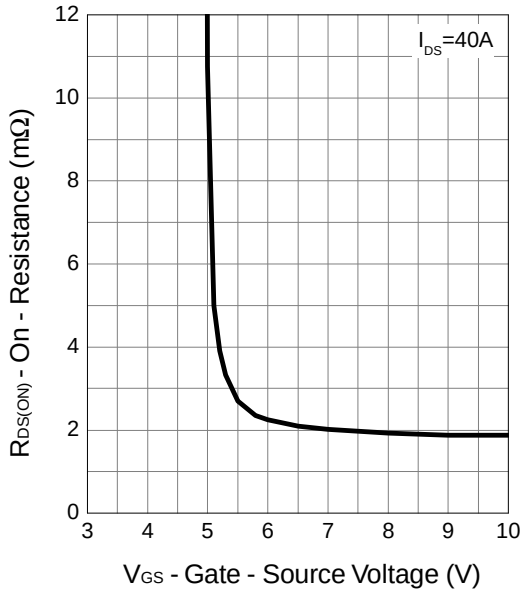
Output Characteristics



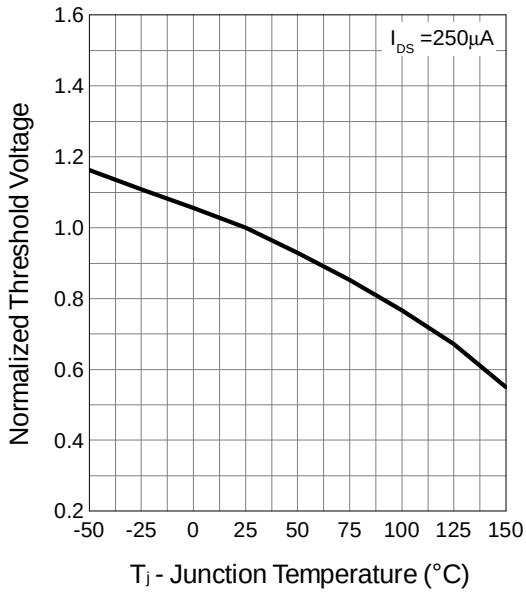
Drain-Source On Resistance



Gate-Source On Resistance

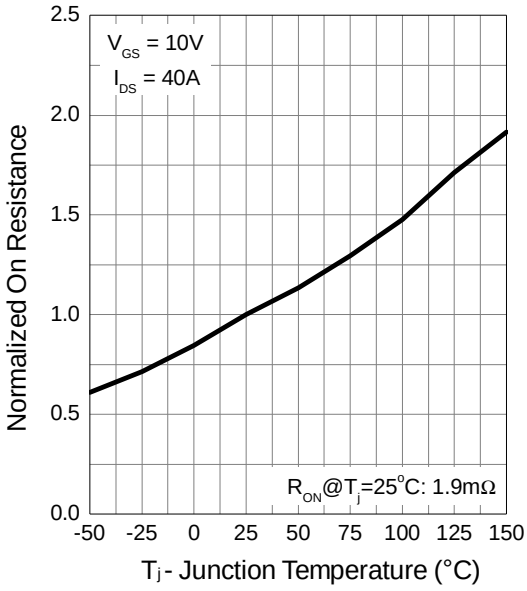


Gate Threshold Voltage

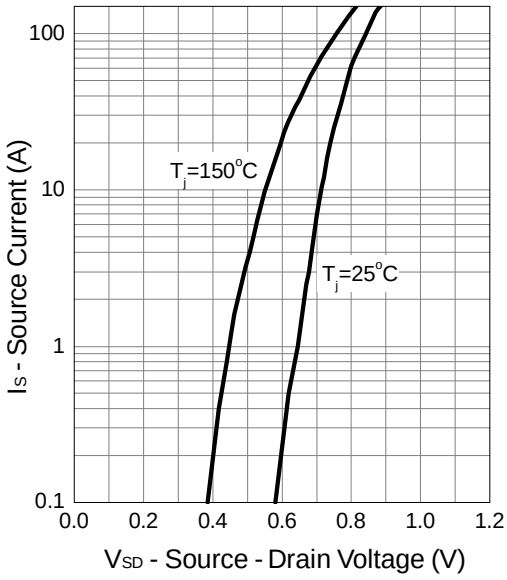


Typical Operating Characteristics (Cont.)

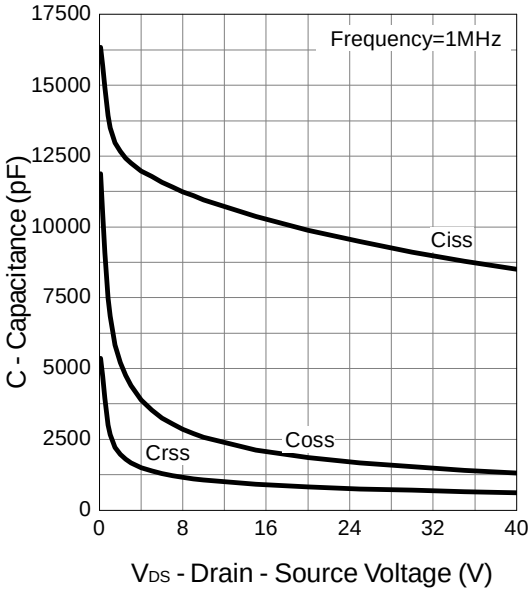
Drain-Source On Resistance



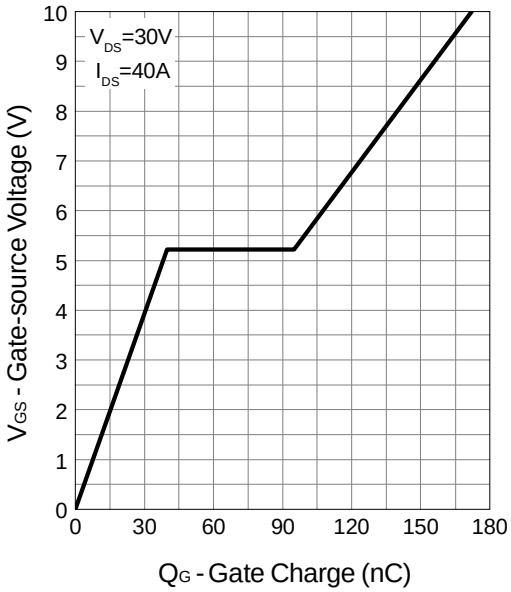
Source-Drain Diode Forward



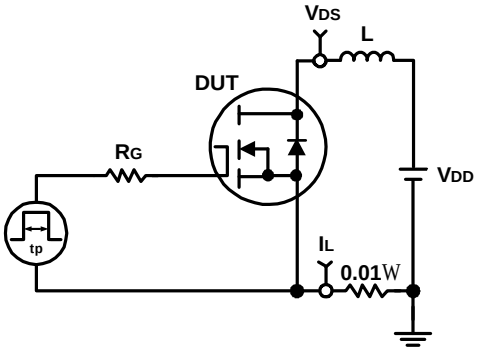
Capacitance

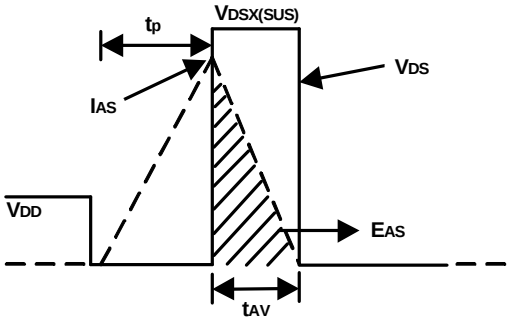


Gate Charge

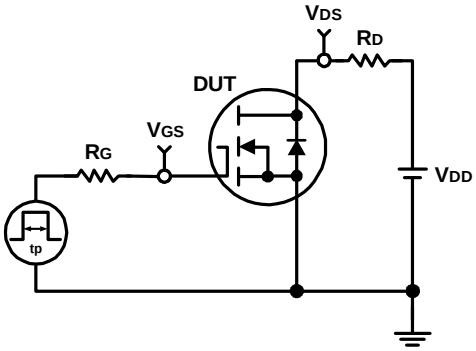


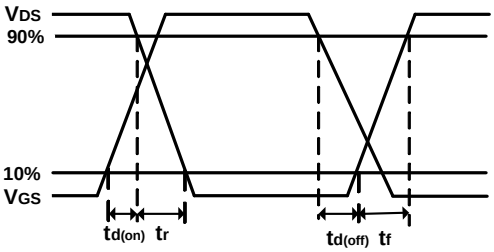
Avalanche Test Circuit and Waveforms





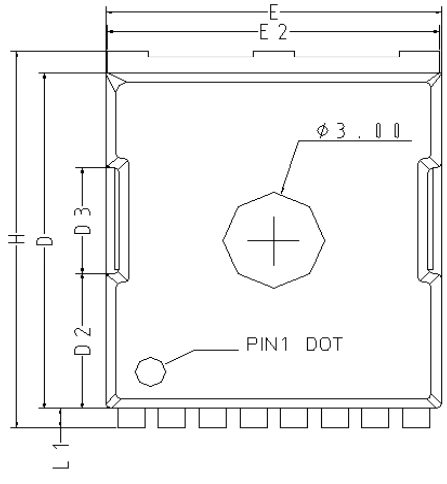
Switching Time Test Circuit and Waveforms



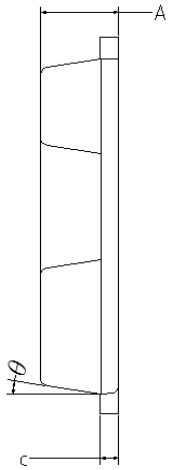


Package Information

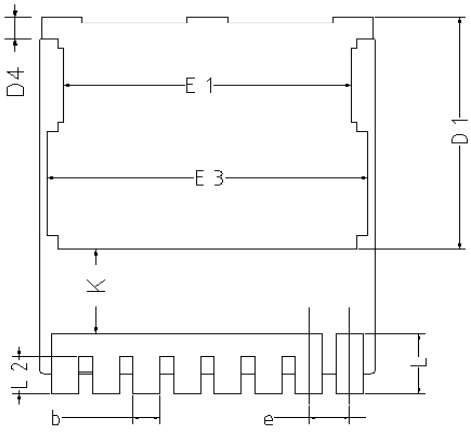
TOLL



Top View



Side View

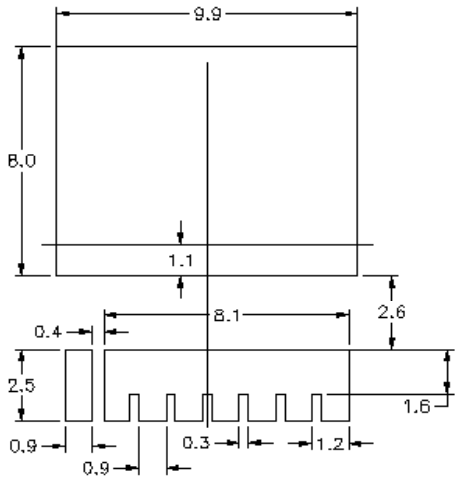


Bottom View

Side View

SYMBOLS	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.20	2.40	0.087	0.094
b	0.70	0.90	0.028	0.035
c	0.40	0.60	0.016	0.024
D	10.23	10.63	0.403	0.419
D1	7.05	7.45	0.278	0.293
D2	3.98	4.38	0.157	0.172
D3	3.10	3.50	0.122	0.138
D4	0.50	0.90	0.020	0.035
E	9.70	10.10	0.382	0.398
E1	8.30	8.70	0.327	0.343
E2	9.60	10.00	0.378	0.394
E3	9.26	9.66	0.365	0.380
H	11.53	11.93	0.454	0.470
e	1.2 BSC		0.0472 BSC	
K	2.43	2.83	0.096	0.111
L	1.65	2.05	0.065	0.081
L1	0.40	0.80	0.016	0.031
L2	0.95	1.35	0.037	0.053
θ	6°	10°	6°	10°

RECOMMENDED LAND PATTERN



UNIT: mm